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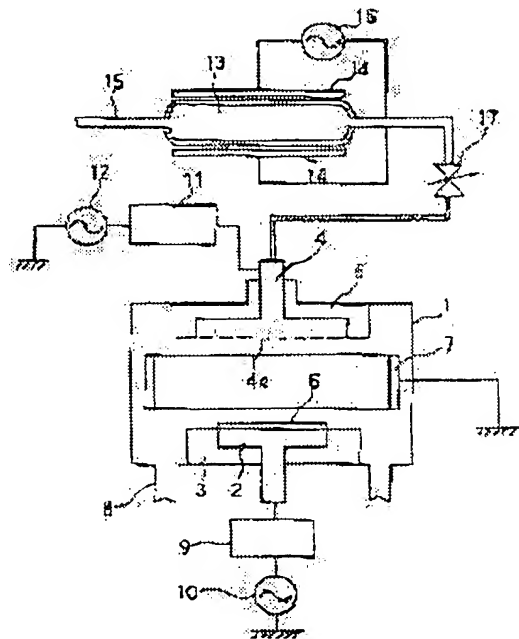
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(54) PLASMA ETCHING DEVICE

(57)Abstract:

PURPOSE: To enable rapid formation of a highly precise pattern wherein foundation is shaved little on a high step pattern by controlling reaction species generation, plasma generation and ion energy control independently.

CONSTITUTION: Reaction species supplied to a plasma generation electrode 4 is controlled by pressure adjustment inside a reaction species generation chamber 13 by a control valve 17 and adjustment of high frequency electric power supplied to a parallel plane electrode 14. A plasma generation means can generate specified plasma by adjusting high frequency electric power of a generation high frequency power supply 12 and controls an amount of ions injected to a substrate 6. An ion energy control means controls energy of ions injected to the substrate 6 by controlling high frequency bias applied to a stage electrode 2 by adjusting high frequency electric power of a high frequency power supply 10 connected to the stage electrode 2. Thereby, etching of high selection and a fast speed can be realized.



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